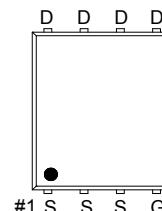
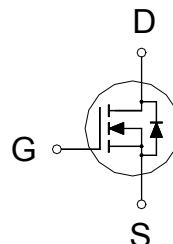


NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
PK6D0BA
PDFN 5x6P
Halogen-Free & Lead-Free
PRODUCT SUMMARY

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ | I_D |
|---------------|--------------|-------|
| 30V | 10.5mΩ | 40A |


G. GATE
D. DRAIN
S. SOURCE
**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

| PARAMETERS/TEST CONDITIONS | | SYMBOL | LIMITS | UNITS |
|--|---------------------------|----------------|------------|-------|
| Drain-Source Voltage | | V_{DS} | 30 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Continuous Drain Current | $T_C = 25^\circ\text{C}$ | I_D | 40 | A |
| | $T_C = 100^\circ\text{C}$ | | 25 | |
| Pulsed Drain Current ¹ | | I_{DM} | 80 | |
| Continuous Drain Current | $T_A = 25^\circ\text{C}$ | I_D | 10 | W |
| | $T_A = 70^\circ\text{C}$ | | 8.3 | |
| Avalanche Current | | I_{AS} | 21 | |
| Avalanche Energy | $L = 0.1\text{mH}$ | E_{AS} | 22 | mJ |
| Power Dissipation | $T_C = 25^\circ\text{C}$ | P_D | 31 | W |
| | $T_C = 100^\circ\text{C}$ | | 12 | |
| Power Dissipation | $T_A = 25^\circ\text{C}$ | P_D | 2 | W |
| | $T_A = 70^\circ\text{C}$ | | 1.3 | |
| Operating Junction & Storage Temperature Range | | T_j, T_{stg} | -55 to 150 | °C |

THERMAL RESISTANCE RATINGS

| THERMAL RESISTANCE | SYMBOL | TYPICAL | MAXIMUM | UNITS |
|----------------------------------|-----------------|---------|---------|--------|
| Junction-to-Ambient ² | $R_{\theta JA}$ | | 60 | |
| Junction-to-Case | $R_{\theta JC}$ | | 4 | °C / W |

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.**ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)**

| PARAMETER | SYMBOL | TEST CONDITIONS | LIMITS | | | UNIT |
|--------------------------------|---------------------|--|--------|------|-----|------|
| | | | MIN | TYP | MAX | |
| STATIC | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$ | 30 | | | V |
| Gate Threshold Voltage | $V_{GS(\text{th})}$ | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 1.3 | 1.75 | 2.3 | |

NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
**PK6D0BA
PDFN 5x6P
Halogen-Free & Lead-Free**

| | | | | | | |
|--|--------------|---|--|------|-----------|-----------|
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0V, V_{GS} = \pm 20V$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 24V, V_{GS} = 0V$ | | | 1 | μA |
| | | $V_{DS} = 20V, V_{GS} = 0V, T_J = 55^{\circ}C$ | | | 10 | |
| Drain-Source On-State Resistance ¹ | $R_{DS(ON)}$ | $V_{GS} = 4.5V, I_D = 13A$ | | 10 | 14 | $m\Omega$ |
| | | $V_{GS} = 10V, I_D = 13A$ | | 7 | 10.5 | |
| Forward Transconductance ¹ | g_{fs} | $V_{DS} = 5V, I_D = 13A$ | | 42 | | S |
| DYNAMIC | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$ | | 529 | | pF |
| Output Capacitance | C_{oss} | | | 142 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 64 | | |
| Gate Resistance | R_g | $V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$ | | 1 | | Ω |
| Total Gate Charge ² | Q_g | $V_{DS} = 15V, V_{GS} = 10V, I_D = 13A$ | | 10.3 | | nC |
| | | | | 6 | | |
| Gate-Source Charge ² | Q_{gs} | | | 1.4 | | |
| Gate-Drain Charge ² | Q_{gd} | | | 3 | | |
| Turn-On Delay Time ² | $t_{d(on)}$ | $V_{DS} = 15V, I_D \geq 13A, V_{GS} = 10V, R_{GEN} = 6\Omega$ | | 15 | | nS |
| Rise Time ² | t_r | | | 13 | | |
| Turn-Off Delay Time ² | $t_{d(off)}$ | | | 21 | | |
| Fall Time ² | t_f | | | 15 | | |
| SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^{\circ}C$) | | | | | | |
| Continuous Current | I_S | | | | 25 | A |
| Forward Voltage ¹ | V_{SD} | $I_F = 13A, V_{GS} = 0V$ | | | 1.2 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 13A, dI_F/dt = 100A/\mu S$ | | 8.2 | | nS |
| Reverse Recovery Charge | Q_{rr} | | | 1.3 | | nC |

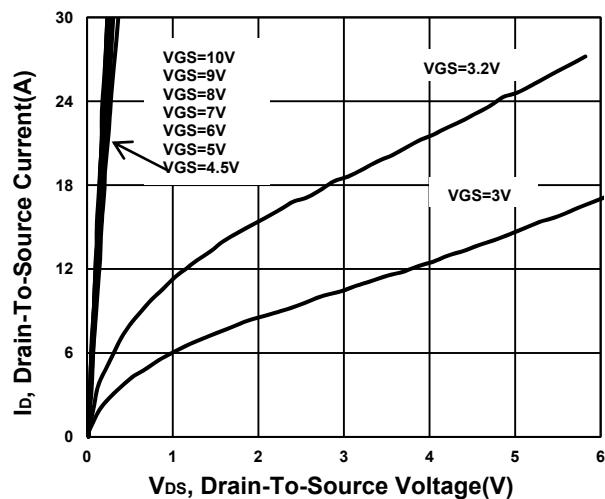
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.

NIKO-SEM

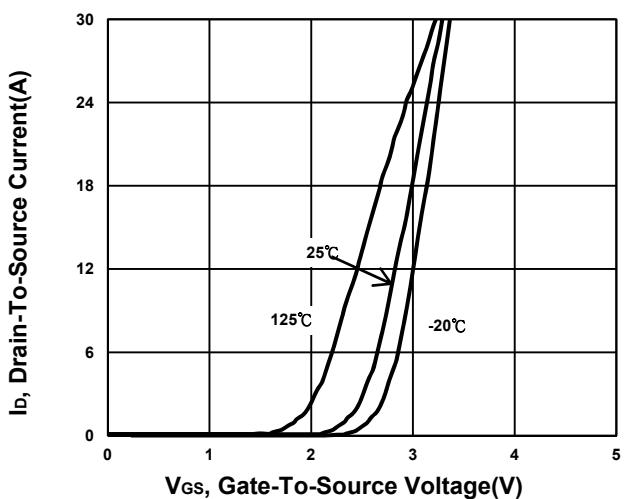
**N-Channel Enhancement Mode
Field Effect Transistor**

PK6D0BA
PDFN 5x6P
Halogen-Free & Lead-Free

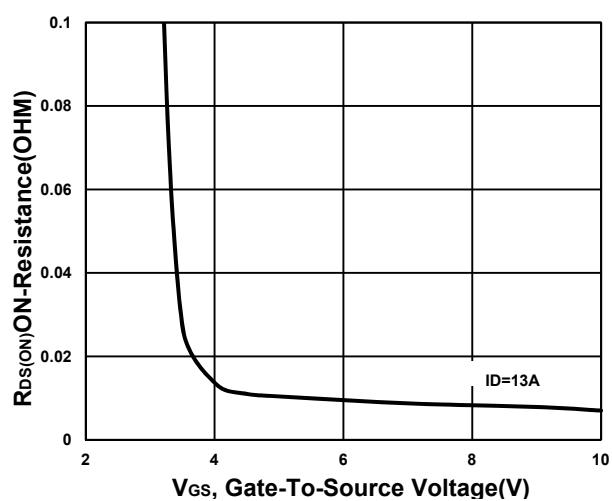
Output Characteristics



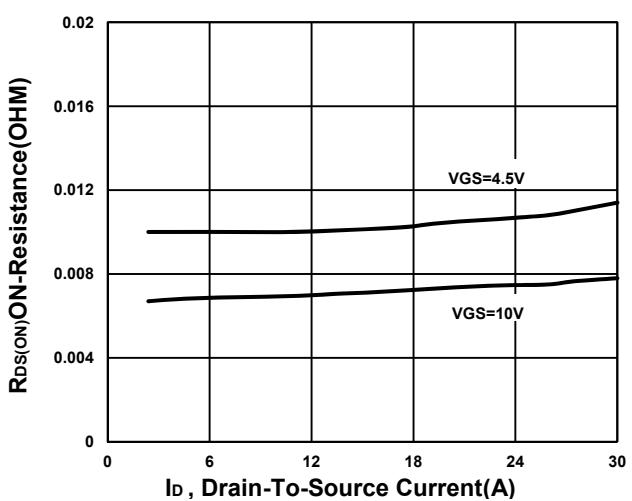
Transfer Characteristics



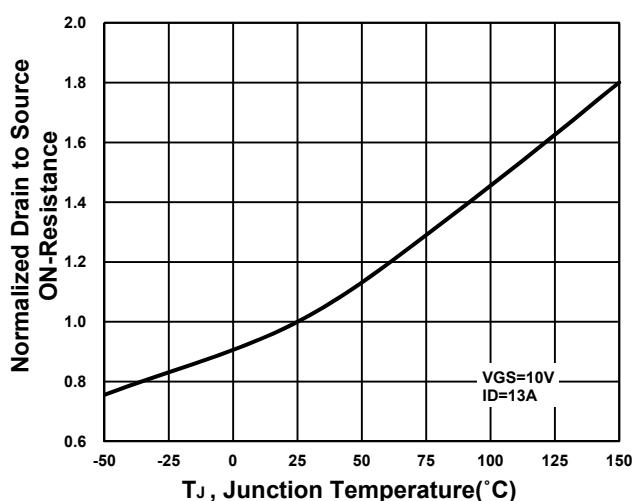
On-Resistance VS Gate-To-Source



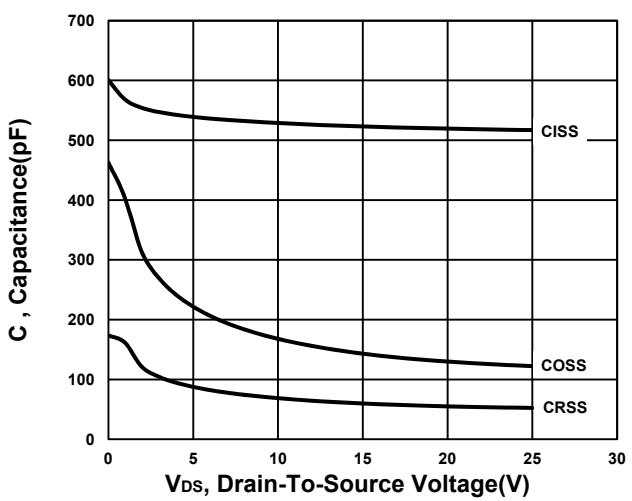
On-Resistance VS Drain Current



On-Resistance VS Temperature



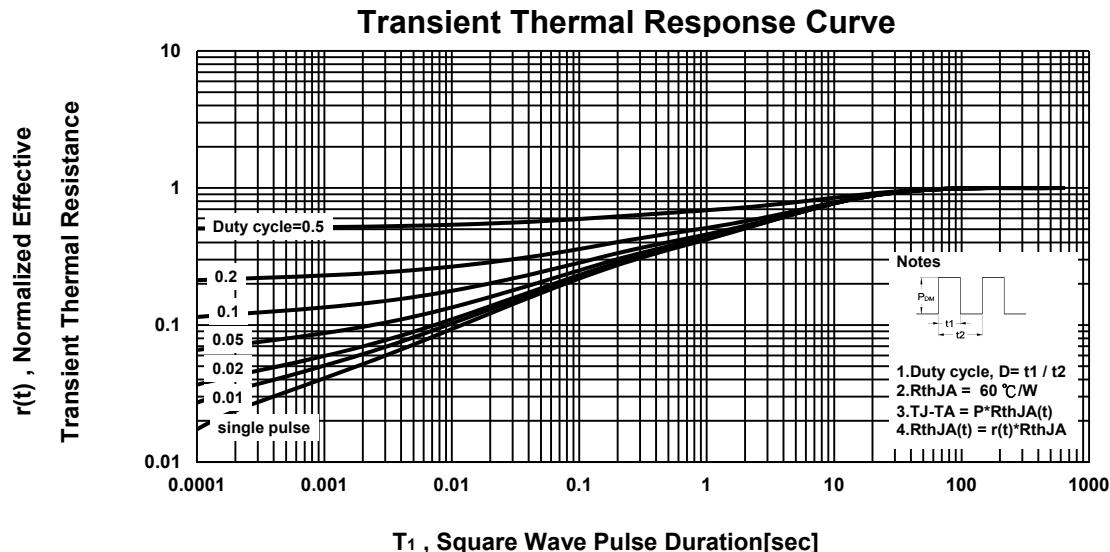
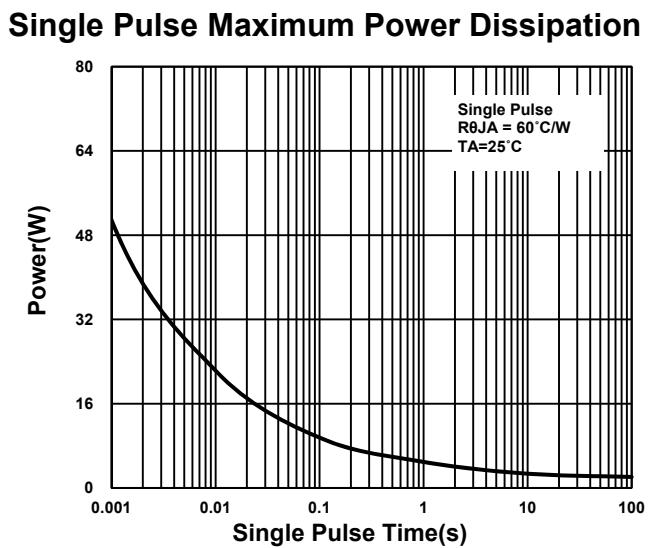
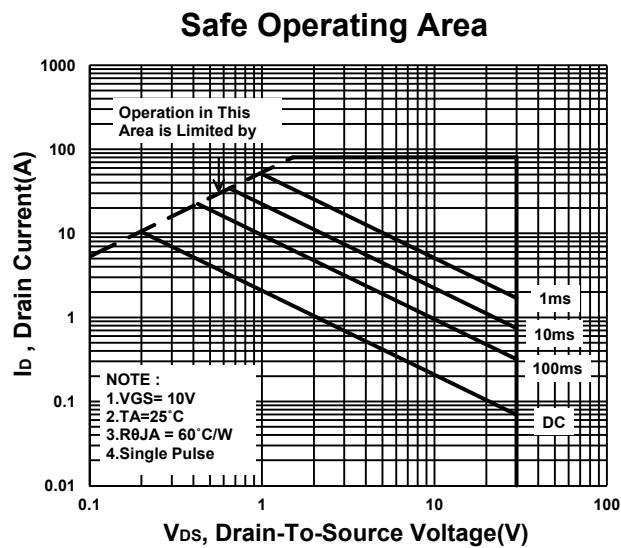
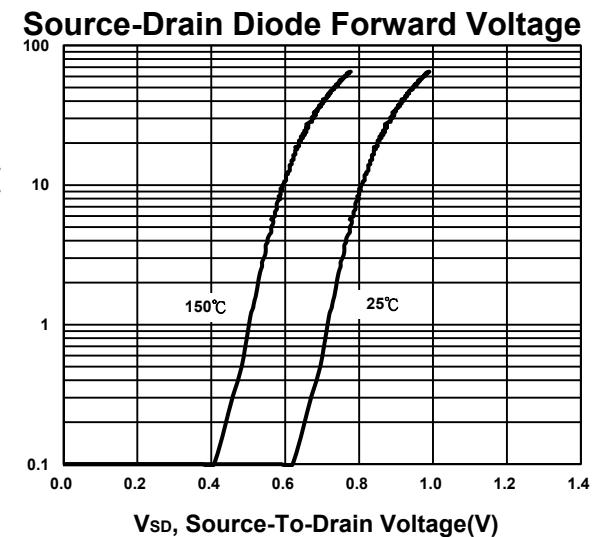
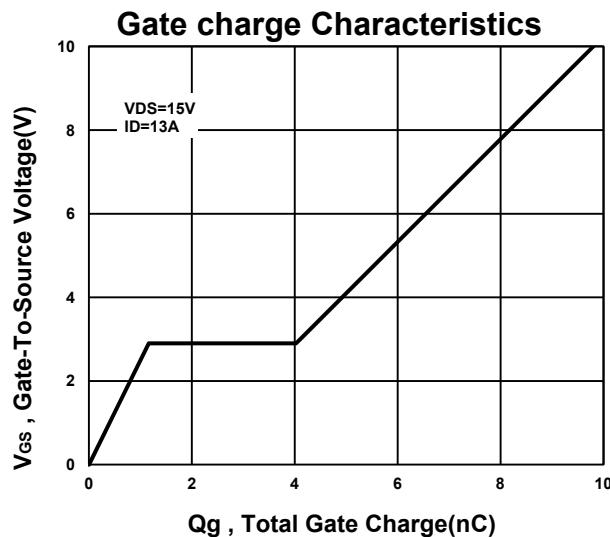
Capacitance Characteristic



NIKO-SEM

**N-Channel Enhancement Mode
Field Effect Transistor**

**PK6D0BA
PDFN 5x6P
Halogen-Free & Lead-Free**



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [NIKO](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)